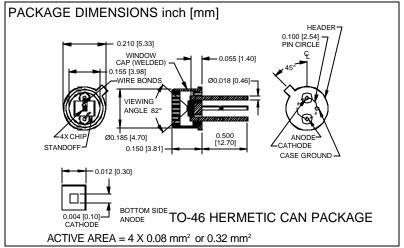
PHOTONIC Silicon Carbide (SiC), Ultra Violet (U.V.) Photodiode DETECTORS INC. Type PDU-S104





FEATURES

DESCRIPTION

The PDU-S104 is a SiC, planar passivated

• 0.14 A/W @ 280 nm High shunt resistance

U.V. photodiode. Spectral range from 200 • 280 nm peak response nm to 400 nm with a 0.08 mm² active area

• Short wavelength resp.

per chip. Four chips packaged in a isolated TO-46 with a U.V. transmitting window can.

APPLICATIONS

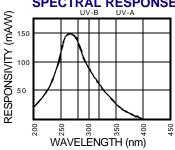
- Flame detectors
- U.V. sensors
- U.V. monitors
- U.V. instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V _{BR}	Reverse Voltage		20	V	
T _{stg}	Storage Temperature	-55	+175	°C	
T _o	Operating Temperature Range	-40	+125	°С	
T _s	Soldering Temperature*		+240	°C	
I	Light Current		0.5	mA	

^{1/16} inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{sc}	Short Circuit Current	H = 1 SUN, 360 nm	30	40		nA
I _D	Dark Current	$H = 0, V_R = 1 V$		2	5	nA
R _{SH}	Shunt Resistance	$H = 0, V_{R} = 10 \text{ mV}$	100	250		$M\Omega$
TC R _{SH}	RSH Temp. Coefficient	$H = 0, V_{R} = 10 \text{ mV}$		-8		%/℃
C _J	Junction Capacitance	$H = 0, V_R = 0 V^{**}$		100	250	pF
λ range	Spectral Application Range	Spot Scan	200		400	nm
λр	Spectral Response - Peak	Spot Scan		280		nm
V _{BR}	Breakdown Voltage	I = 10 µ A	10	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		6x10 ⁻¹⁴		W/√ Hz
tr	Response Time	$RL = 1 K\Omega V_R = 10 V$		20	50	nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1MHz [FORM NO. 100-PDU-S104 REV N/C]